ABSTRACT

A semiconductor device includes a substrate including a first active pattern, a first channel pattern on the first active pattern, the first channel pattern including first, second, and third semiconductor patterns spaced apart from one another and vertically stacked, a first source/drain pattern connected to the first to third semiconductor patterns, and a gate electrode on the first to third semiconductor patterns. The first source/drain pattern includes a first protrusion protruding toward the first semiconductor pattern, a second protrusion protruding toward the second semiconductor pattern, and a third protrusion protruding toward the third semiconductor pattern. A width of the second protrusion is greater than a width of the first protrusion. A width of the third protrusion is greater than the width of the second protrusion.

FIG. 6A